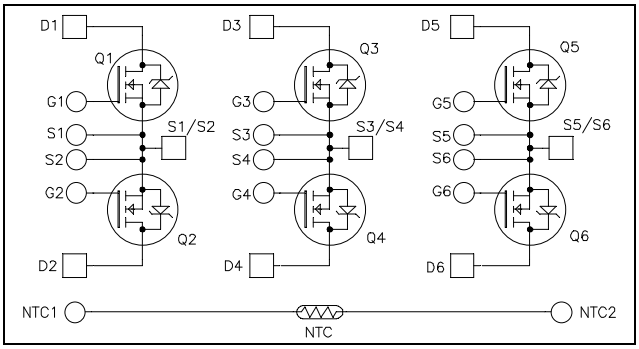
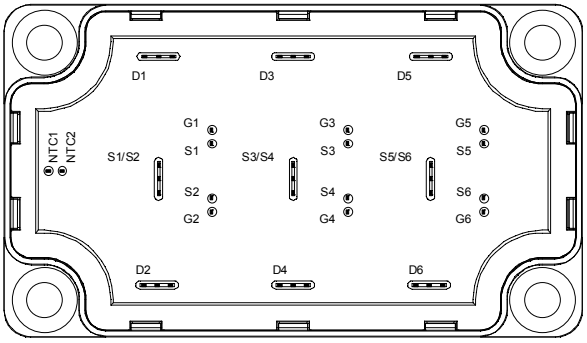
APTC60TDUM24TPG

Triple dual Common Source Super Junction MOSFET Power Module

V_{DSS} = 600V
R_{DSon} = 24mΩ max @ Tj = 25°C
I_D = 95A @ Tc = 25°C





Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- COOLMOS Power Semiconductors
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		600	V
I_D	Continuous Drain Current	T_c = 25°C	95	A
		T_c = 80°C	70	
I_{DM}	Pulsed Drain current		260	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		24	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	462	W
I_{AR}	Avalanche current (repetitive and non repetitive)		15	A
E_{AR}	Repetitive Avalanche Energy		3	mJ
E_{AS}	Single Pulse Avalanche Energy		1900	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V,V_{DS} = 600V	T_j = 25°C			350	µA
		V_{GS} = 0V,V_{DS} = 600V	T_j = 125°C			600	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 47.5A				24	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 5mA		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				200	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V ; V_{DS} = 25V f = 1MHz		14.4		nF
C_{oss}	Output Capacitance			17		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 300V I_D = 95A		300		nC
Q_{gs}	Gate – Source Charge			68		
Q_{gd}	Gate – Drain Charge			102		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{GS} = 10V V_{Bus} = 400V I_D = 95A R_G = 2.5Ω		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			100		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 10V ; V_{Bus} = 400V I_D = 95A ; R_G = 2.5Ω		1350		µJ
E_{off}	Turn-off Switching Energy			1040		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 10V ; V_{Bus} = 400V I_D = 95A ; R_G = 2.5Ω		2200		µJ
E_{off}	Turn-off Switching Energy			1270		

Source - Drain diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_S	Continuous Source current (Body diode)		Tc = 25°C		95		A
			Tc = 80°C		70		
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 95A				1.2	V
dv/dt	Peak Diode Recovery ❶					4	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 95A V_R = 350V di_S/dt = 200A/µs	T_j = 25°C		600		ns
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		34		µC

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 95A di/dt ≤ 200A/µs $V_R \le V_{DSS}$ $T_j \le$ 150°C

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance					0.27	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

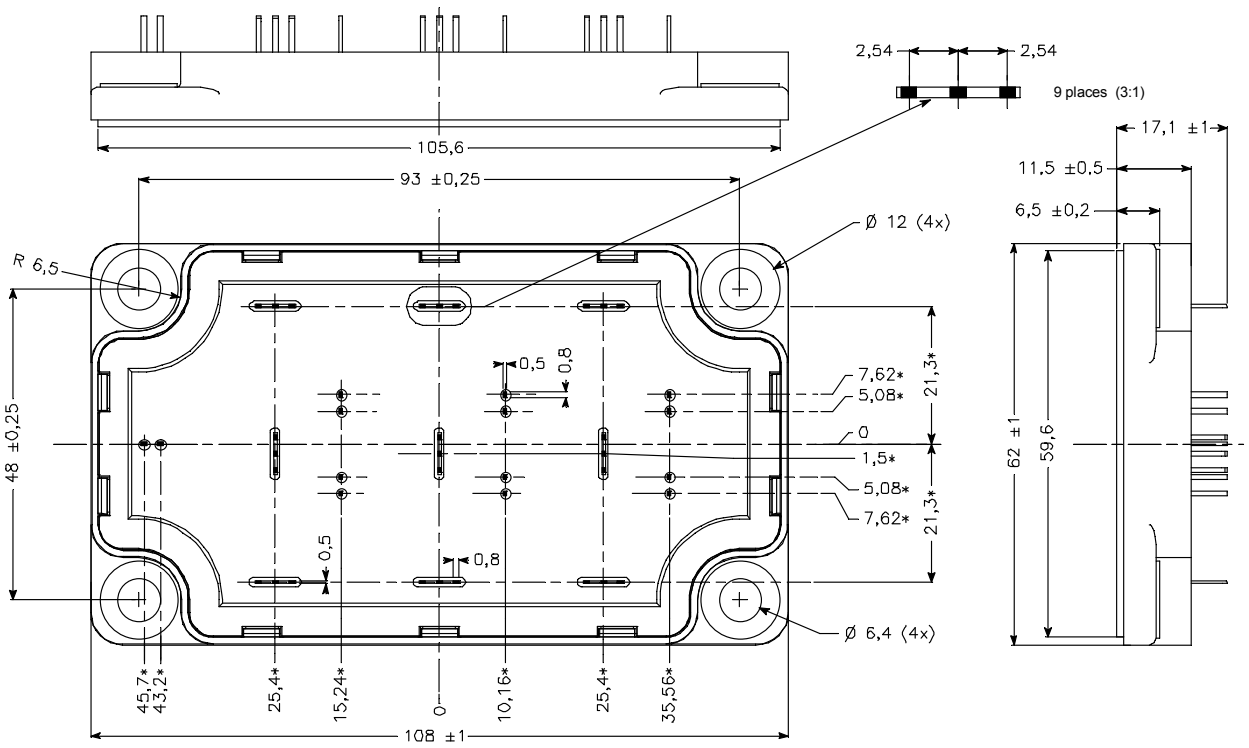
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

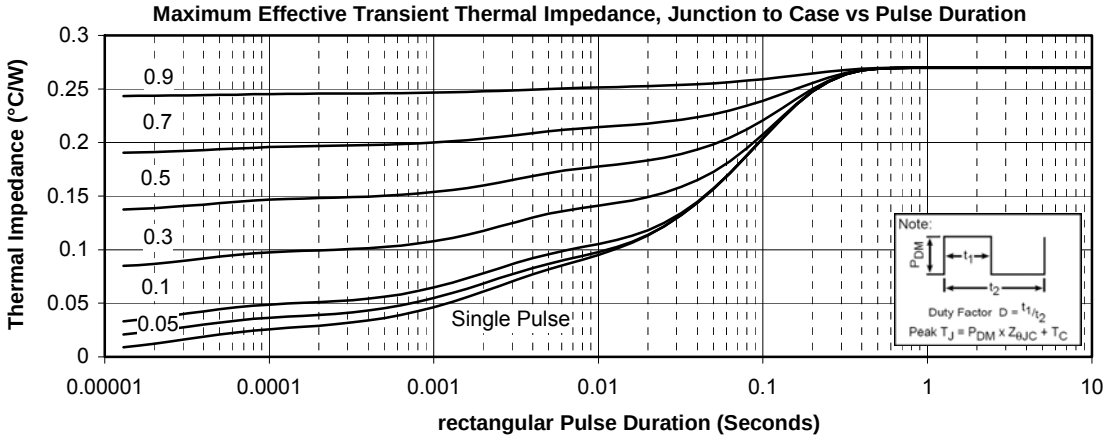
SP6-P Package outline (dimensions in mm)

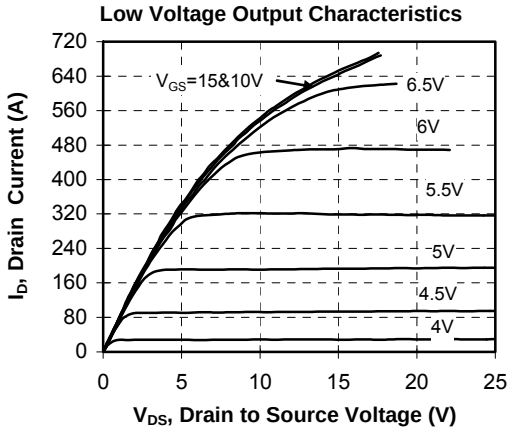


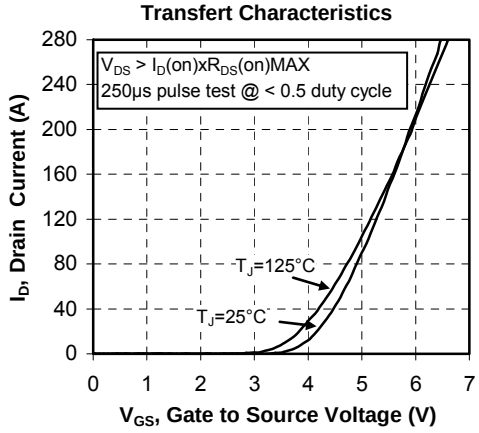
ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : ⊕Ø1

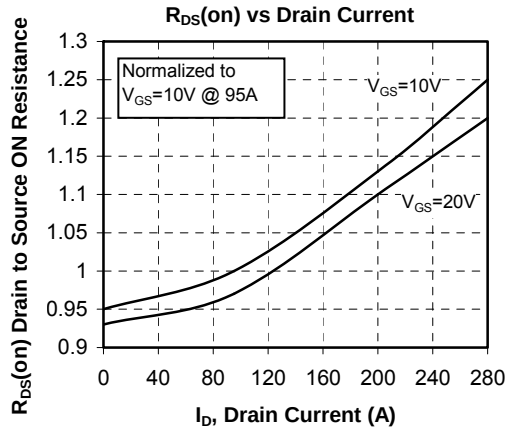
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

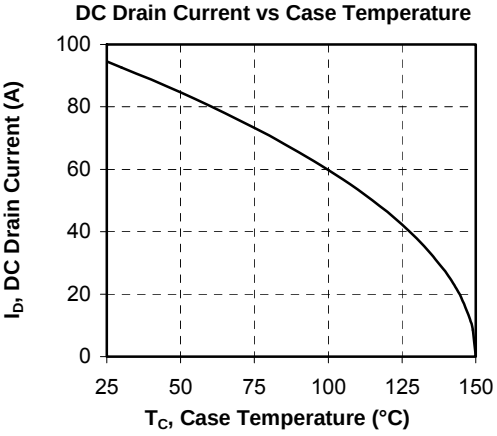
Typical Performance Curve



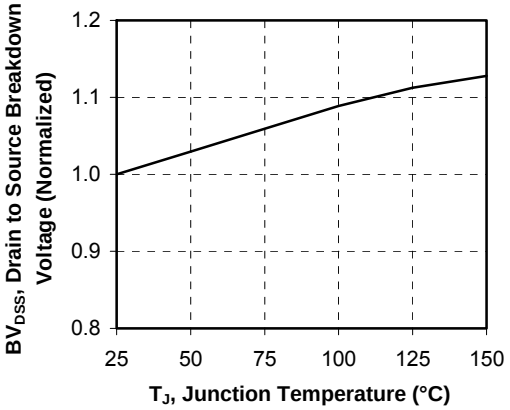




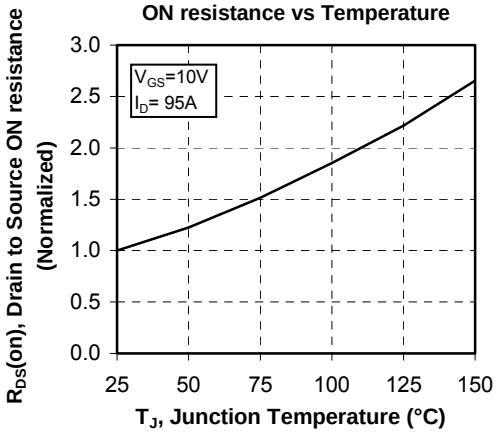




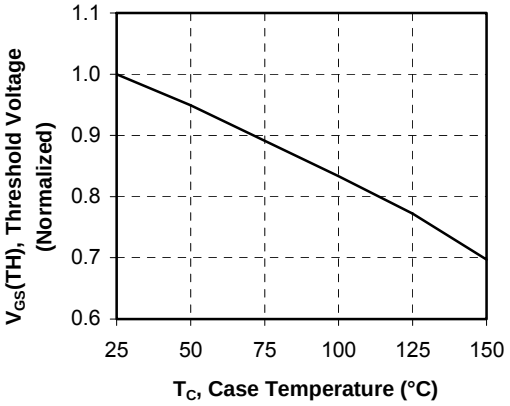
Breakdown Voltage vs Temperature



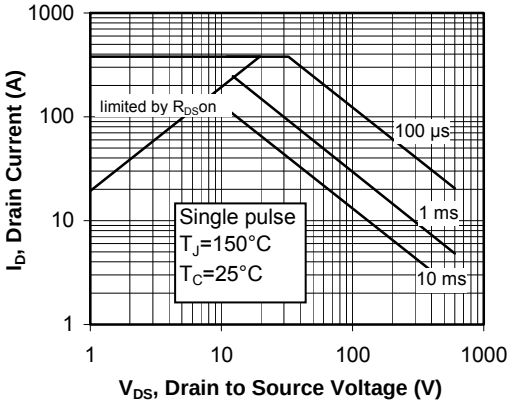
ON resistance vs Temperature



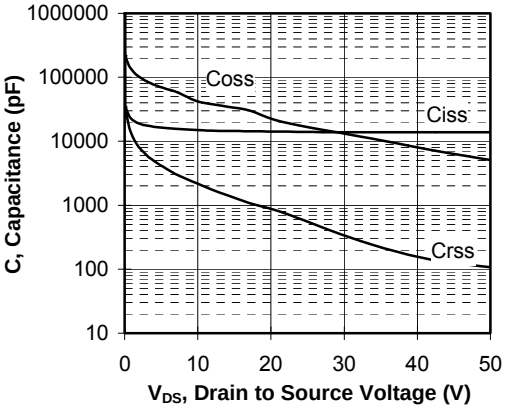
Threshold Voltage vs Temperature



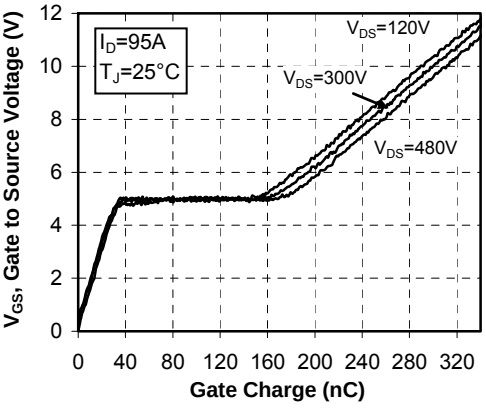
Maximum Safe Operating Area

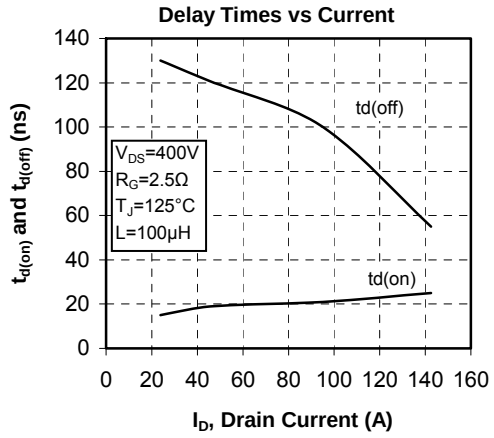


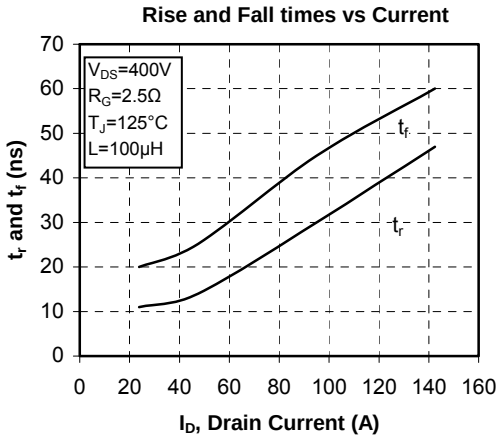
Capacitance vs Drain to Source Voltage

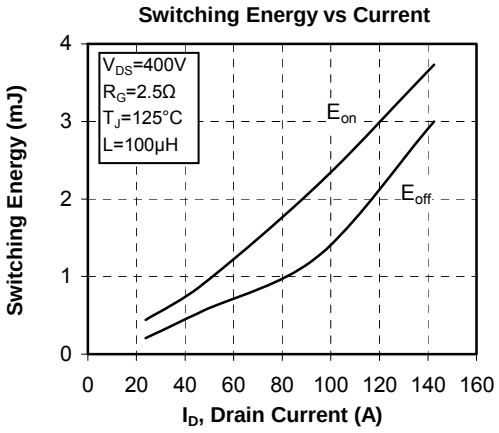


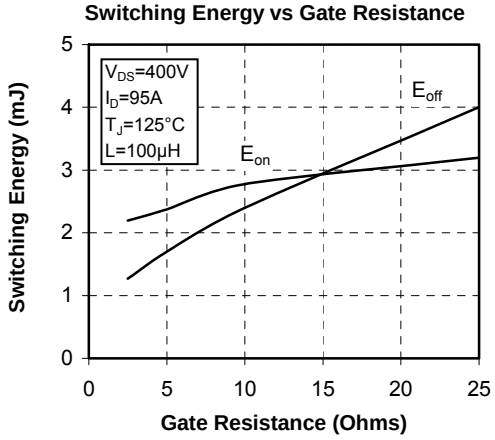
Gate Charge vs Gate to Source Voltage

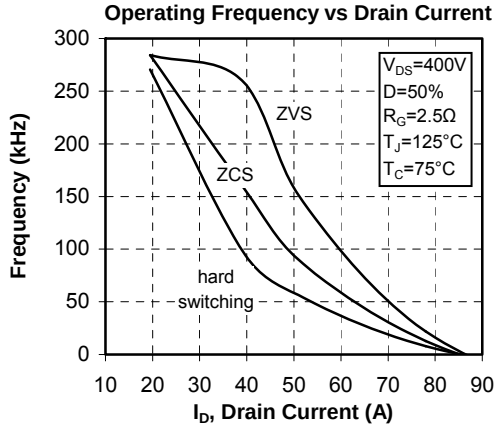


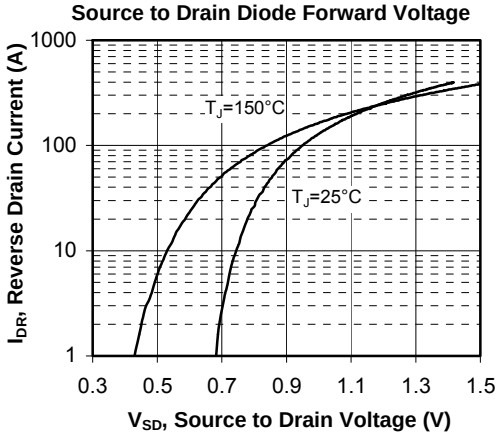












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